

L Number	Hits	Search Text	DB	Time stamp
1	2	5824599.pn. 6020266.pn.	USPAT; US-PGPUB	2004/03/04 15:39
2	3585	257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.	USPAT; US-PGPUB	2004/03/04 16:33
3	0	((257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and ((gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os)) same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	USPAT; US-PGPUB	2004/03/04 17:18
4	118	((257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and (gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os))	USPAT; US-PGPUB	2004/03/04 16:39
5	14	((257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and (polysilicon with gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os))	USPAT; US-PGPUB	2004/03/04 16:39
6	15	((gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os)) same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	USPAT; US-PGPUB	2004/03/04 16:55
7	35	((257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and (gate same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	USPAT; US-PGPUB	2004/03/04 17:28
8	380	(gate same ((plug contact) with (copper cu)) same (source drain))	USPAT; US-PGPUB	2004/03/04 17:29
9	13	(gate with ((plug contact) near2 (copper cu)) with (source drain))	USPAT; US-PGPUB	2004/03/04 17:34
10	26	438/620.ccls. and ((plug contact) with (copper cu))	USPAT; US-PGPUB	2004/03/04 17:36
11	547	((257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and ((copper cu silver ag gold au platinum pt) same ((rhodium rh ruthenium ru iridium ir osmium os platinum pt) with (palladium pd cobalt co nickel ni titanium ti)))	USPAT; US-PGPUB	2004/03/04 18:05
12	1	((insulat\$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch\$4 match\$4))) and ((atom\$2 near (radius radii)) (bond\$4 near energy))	EPO; JPO; DERWENT; IBM_TDB	2004/03/04 18:06
13	27	((atom\$2 near (radius radii)) (bond\$4 near energy)) and (semiconductor silicon si wafer substrate) and (copper cu) and (rhodium rh ruthenium ru iridium ir osmium os platinum pt)	EPO; JPO; DERWENT; IBM_TDB	2004/03/04 18:06
14	7	(semiconductor silicon si wafer substrate) and ((interconnect\$5 metal\$1is\$7 metal\$1iz\$7) same ((platinum pt) near4 (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")) same ((osmium os) with (palladium pd cobalt co nickel ni titanium ti) with (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer"))	USPAT; US-PGPUB	2004/03/04 18:08
15	241	((atom\$2 near (radius radii)) (bond\$4 near energy)) and (semiconductor silicon si wafer substrate) and ((copper cu) same (rhodium rh ruthenium ru iridium ir osmium os platinum pt) same (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer"))	USPAT; US-PGPUB	2004/03/04 18:11
17	199	(semiconductor silicon si wafer substrate) and ((insulat\$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch\$4 match\$4))) and ((atom\$2 near (radius radii)) (bond\$4 near energy))	USPAT; US-PGPUB	2004/03/04 18:11

18	365	(semiconductor silicon si wafer substrate) and (((interconnect\$5 metal\$1is\$7 metal\$1iz\$7) same ((copper cu silver ag gold au) near4 (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")) same ((rhodium rh ruthenium ru iridium ir osmium os platinum pt) with (palladium pd cobalt co nickel ni titanium ti) with (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer") with (element constituent consist\$3 compris\$3 atom metal)))	USPAT; US-PGPUB	2004/03/04 18:11
16	135	((insulat\$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch\$4 match\$4)) (atom\$2 near (radius radii)) (bond\$4 near energy)) and ((film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer") with (conduct\$5 platinum pt copper cu silver ag gold au rhodium rh ruthenium ru iridium ir osmium os palladium pd cobalt co nickel ni titanium ti))	EPO; JPO; DERWENT; IBM_TDB	2004/03/04 18:20